Type designations

Typenbezeichnungen

Thyristors

T 930 S 18 T M C

T	symmetrically blocking thyristor
A	asymmetrically blocking thyristor
930	limiting average forward current (A) at tc= 85° C
0	Ceramic disc W
1	Ceramic disc P
4	Epoxy disc 19 mm high
6	Epoxy disc 35 mm high
7	Epoxy disc 8 mm high
8	Epoxy disc 14 mm high
9	Epoxy disc 26 mm high

2.Letter

S	fast thyristor, gate-cathode interdigitated
F	fast thyristor, central gate
N	phase control thyristor
18	limiting repetitive peak forward and reverse off-state voltage in 100 V, 18 = 1800 V (A: repetitive peak forward off-state voltage)

3.Letter

	anode:	cathode:
B	metric thread	cable
C	metric thread	solder pin
E	flat base	cable
F	TO 220 case	
T	disc	

4.Letter

A	8 µs
B	10 µs
C	12 µs
D	15 µs
S	18 µs
E	20 µs
F	25 µs
G	30 µs
K	40 µs
M	50 µs
P	55 µs
N	60 µs
T	80 µs
U	120 µs
O	no guaranteed max. value
1	see data sheet
2	see data sheet

5.Letter

	critical rate of rise forward voltage, thyristors for line commutated converters:	
B	50 V/µs	
C	500 V/µs	
F	1000 V/µs	
G	1500 V/µs	
H	2000 V/µs	
	thyristors for self-commutated converters: critical rate of rise of forward voltage	
	according to DIN IEC 747-6:	immediately after turn-off:
B	50 V/µs	50 V/µs
C	500 V/µs	500 V/µs
F	1000 V/µs	1000 V/µs
L	500 V/µs	50 V/µs
M	1000 V/µs	500 V/µs
N	1000 V/µs	50 V/µs

Rectifier

D 1809 N 32

D	diode
1809	limiting average current (A) as a rule at tc = 100° C
N	rectifier diode: anode on case or press-pack
K	cathode on case
S	fast rectifier diode: anode on case or press-pack
U	cathode on case
32	limiting repetitive peak reverse voltage in 100 V

mechanical construction:

A	metric thread	wire
B	metric thread	cable
C	stud	solder pin
E	flat-base	cable
T	press-pack	

A	Avalanche Diode anode / case
B	Avalanche Diode cathode / case

Half-controlled thyristor modules

TD 121 N 18 K O F -A

TD,DT	with 1 symmetric thyristor and 1 diode
AD	with 1 asymmetric thyristor and 1 diode
	(for circuit see outline)
121	limiting average on-state current (A), tc = 85° C
N	phase control thyristor and retifier diode
F	fast thyristor and fast diode
S	fast thyristor with interdigitated gate and fast diode
18	repetitive peak-off-state voltage in 100 V
K	mech. constr.: pressure contact
O	turn-off time (see thyristors)
F	critical rate of rise of off-state voltage
-A	special design with common anode
-K	special design with common cathode

IGBT modules Type designation

IGBT & Diode: IHM/IHV & all new eupec modules

FF 800 R 17 K F 6 D B2

FF	Dual Switch
FZ	Single Switch
FS	3-phase full Bridge
FP	Power integrated Modul
F4-	One phase bridge
FD	Chopper config.
DD	Dual Diode
	(for circuit see outline)
800	Max. DC-collector current (A)
R	Reverse conducting
S	Fast Short Tail IGBT Chip
17	Collector-emitter-voltage in 100 V
K	Mechanical construction: Module
F	Fast switching IGBT Chip
L	Low Loss IGBT Chip
S	Short Tail IGBT Chip
E	Low Sat & fast IGBT^3 Chip
1..n	Internal reference number
C	With EmCon diode
D	Higher rated diode
B1..n	Construction variation
S1..n	Electrical selection

IGBT & Diodes: BSM modules

BSM 100 GB 120 D N2 K

B	Silicon
S	Type: S=Switch, Y = Diode
M	Module
100	current rating I_C = 100 A
G	technology: G = IGBT-technology
B	Configuration:
	A = single switch / diode
	B = Halfbridge
	D = 3-phase full bridge
	T = Tripack (3 single switches)
	P = Power Integrated Module
	AL=Chopper, diode conn. to collector
	AR=Chopper, diode conn. to emitter
120	max. coll.-emitter-voltage in 10V
D	with fast internal diode
N	low inductance module design
L	Low Loss IGBT chip
2	2nd generation silicon
K	design variation
G	design variation
S	collector sense
E	xxxx special type with codo-no.